

HAT2200R

Silicon N Channel Power MOS FET
Power Switching

REJ03G0232-0200Z

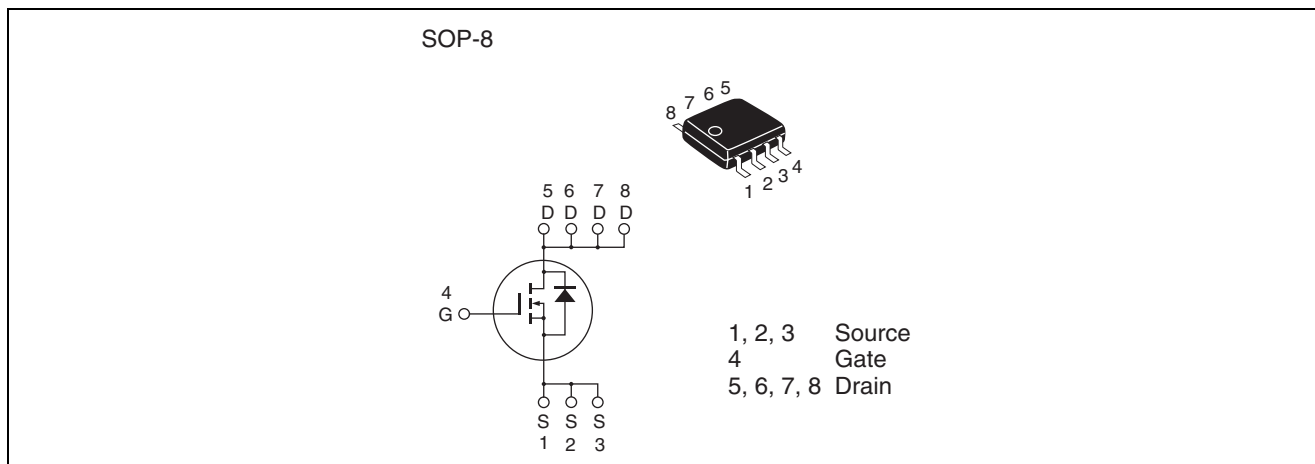
Rev.2.00

Apr.05.2004

Features

- Capable of 8 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
 $R_{DS(on)} = 22 \text{ m}\Omega$ typ. (at $V_{GS} = 10 \text{ V}$)

Outline



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	100	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	8	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	64	A
Body-drain diode reverse drain current	I_{DR}	8	A
Avalanche current	I_{AP} ^{Note 2}	8	A
Avalanche energy	E_{AR} ^{Note 2}	6.4	mJ
Channel dissipation	P_{ch} ^{Note3}	2.5	W
Channel to Ambient Thermal Impedance	θ_{ch-a} ^{Note3}	50	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$ 2. Value at Tch = 25°C, $R_g \geq 50 \Omega$ 3. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), $PW \leq 10s$

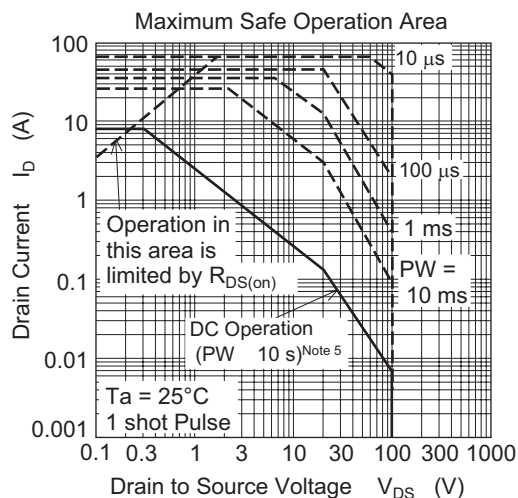
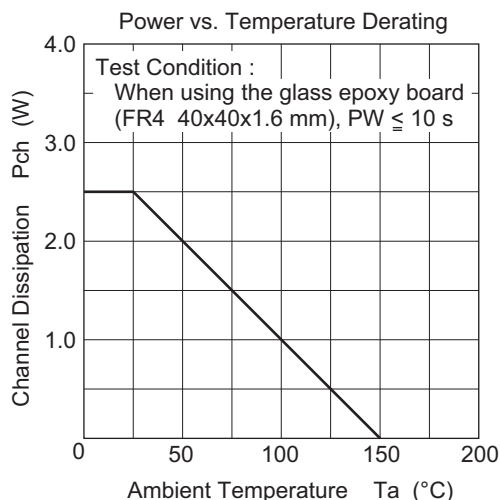
Electrical Characteristics

(Ta = 25°C)

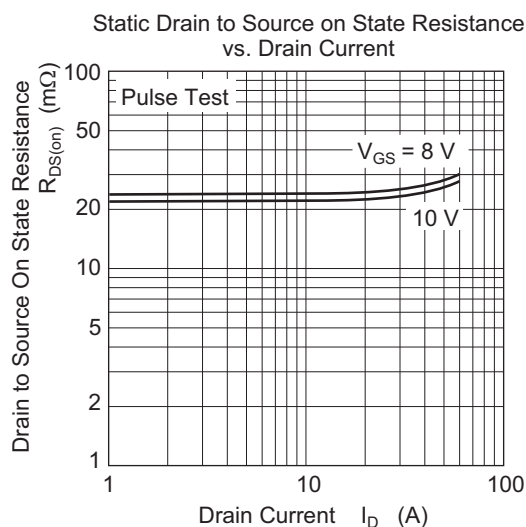
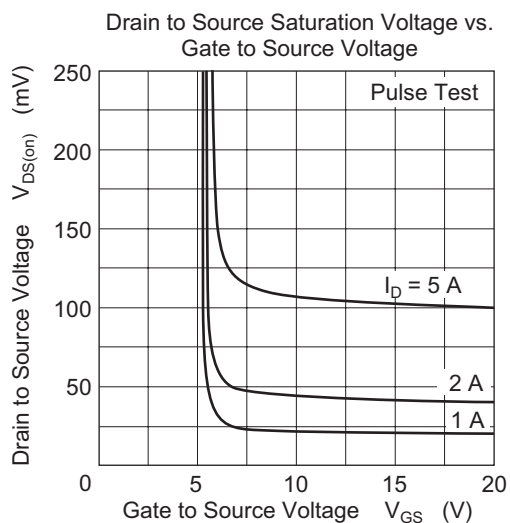
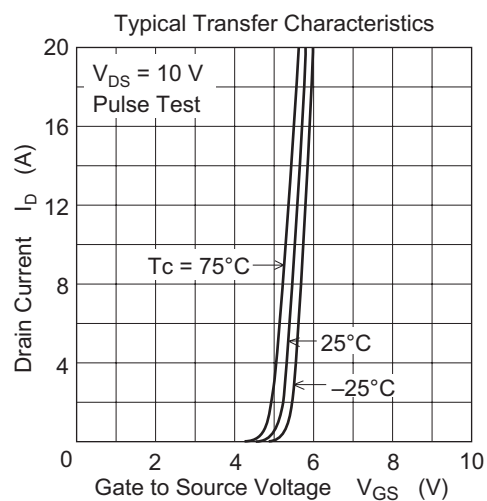
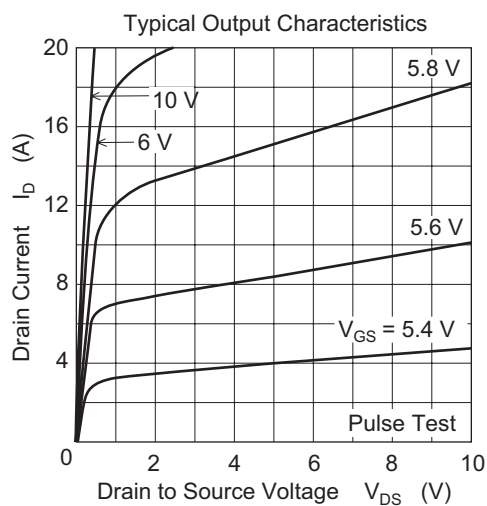
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 100 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.5	—	5.0	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	22	28	mΩ	$I_D = 4 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	23	33	mΩ	$I_D = 4 \text{ A}$, $V_{GS} = 8 \text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	8	14	—	S	$I_D = 4 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	2300	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	280	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	90	—	pF	$f = 1 \text{ MHz}$
Gate Resistance	R_g	—	1.3	—	Ω	
Total gate charge	Q_g	—	32	—	nC	$V_{DD} = 50 \text{ V}$
Gate to source charge	Q_{gs}	—	12	—	nC	$V_{GS} = 10 \text{ V}$
Gate to drain charge	Q_{gd}	—	8	—	nC	$I_D = 8 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	16	—	ns	$V_{GS} = 10 \text{ V}$, $I_D = 4 \text{ A}$
Rise time	t_r	—	4	—	ns	$V_{DD} \cong 30 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	32	—	ns	$R_L = 7.5 \Omega$
Fall time	t_f	—	4.5	—	ns	$R_g = 4.7 \Omega$
Body-drain diode forward voltage	V_{DF}	—	0.79	1.03	V	$I_F = 8 \text{ A}$, $V_{GS} = 0$ ^{Note4}
Body-drain diode reverse recovery time	t_{rr}	—	45	—	ns	$I_F = 8 \text{ A}$, $V_{GS} = 0$ $diF/dt = 100 \text{ A}/\mu s$

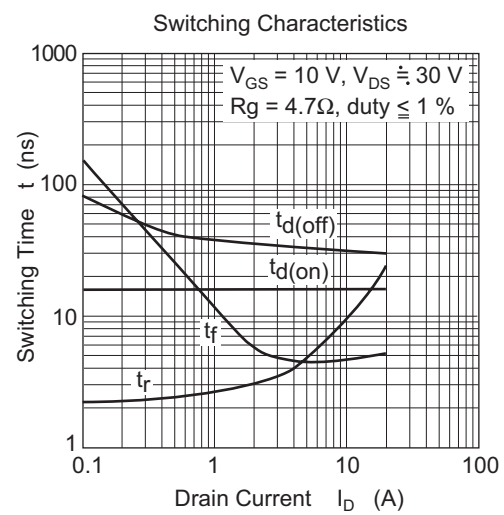
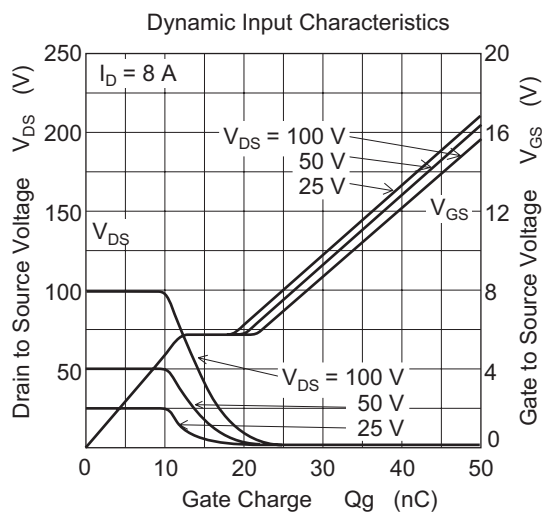
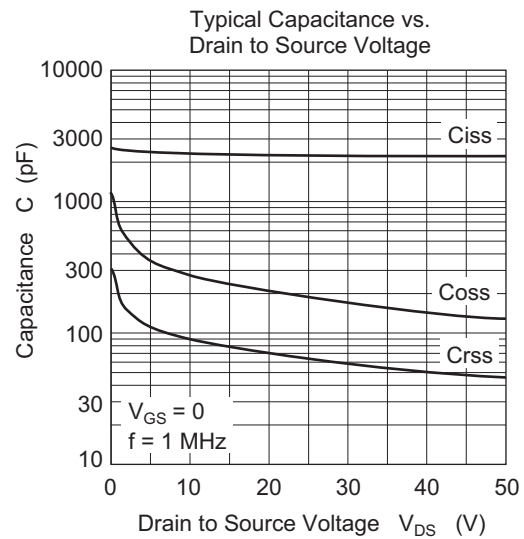
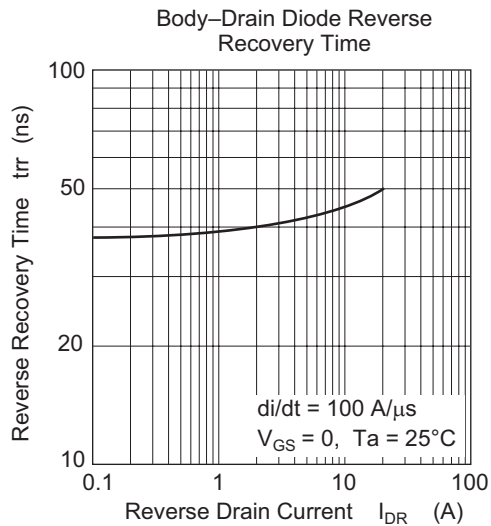
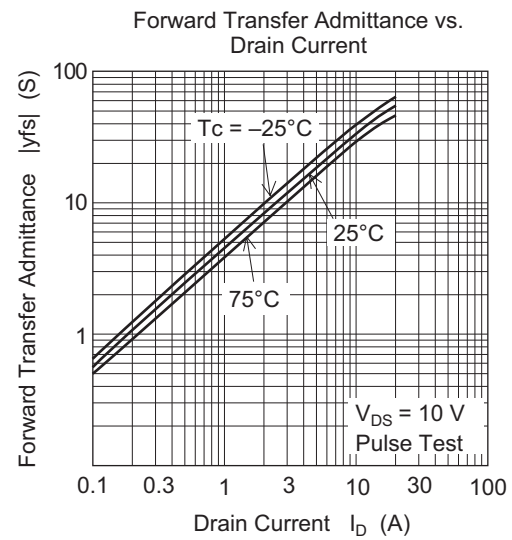
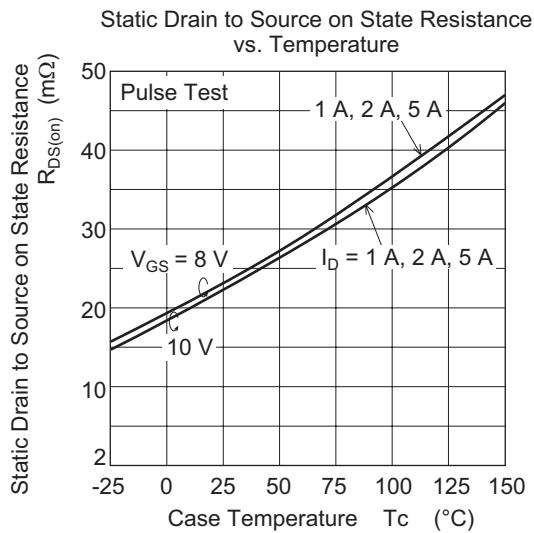
Notes: 4. Pulse test

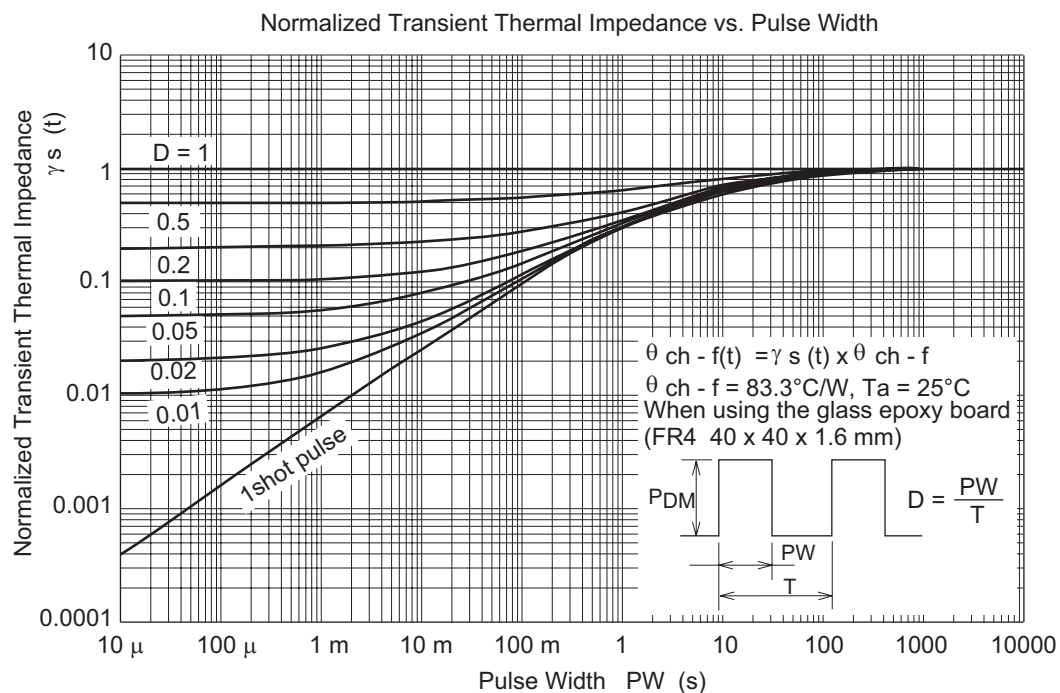
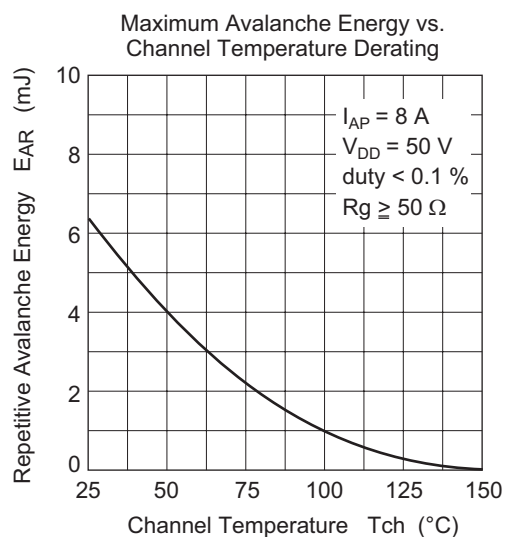
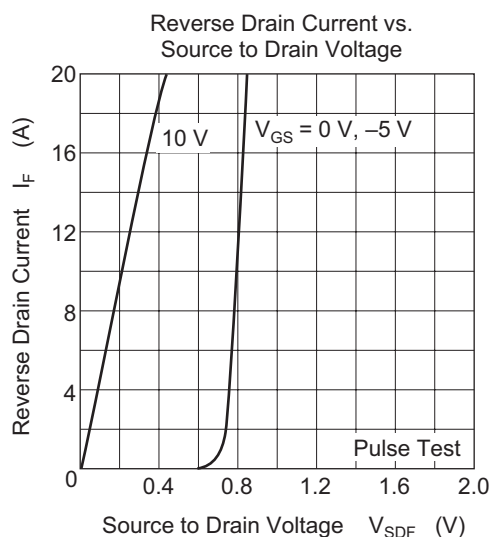
Main Characteristics



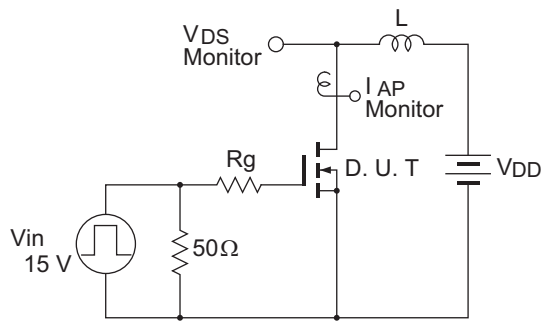
Note 5 :

When using the glass epoxy board
(FR4 40x40x1.6 mm)

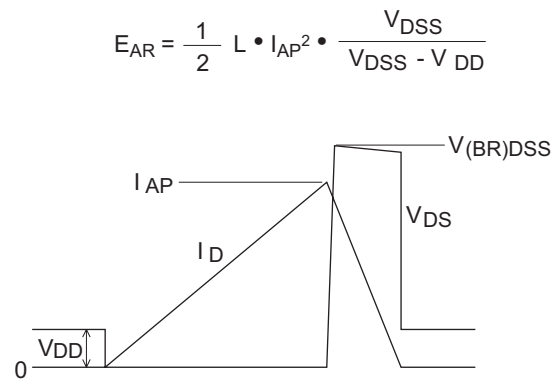




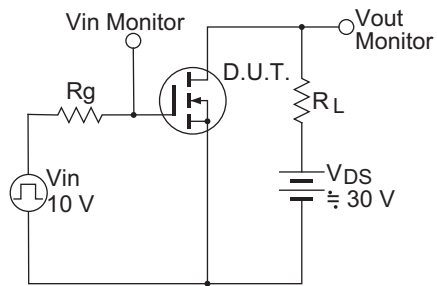
Avalanche Test Circuit



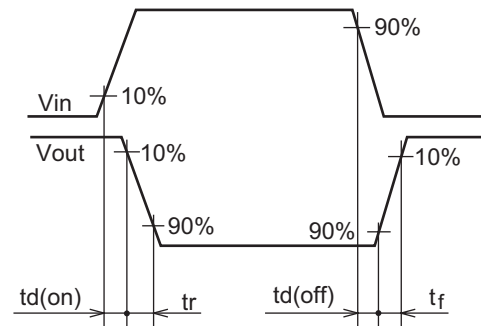
Avalanche Waveform



Switching Time Test Circuit

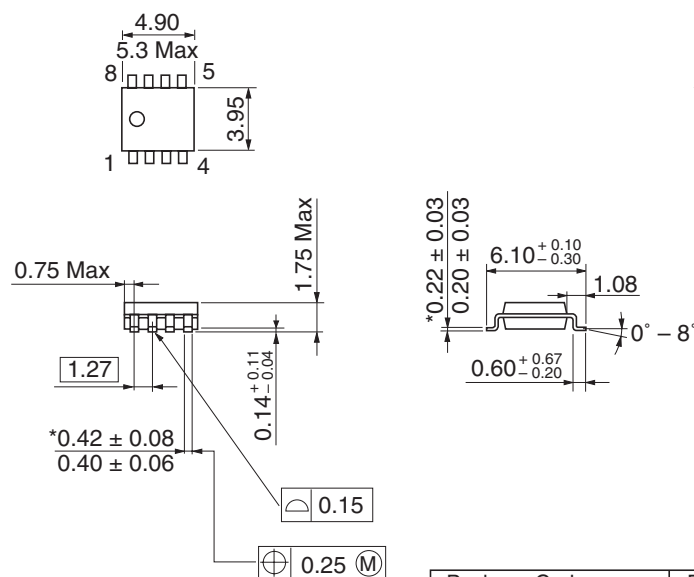


Switching Time Waveform



Package Dimensions

As of January, 2003
Unit: mm



*Dimension including the plating thickness
Base material dimension

Package Code	FP-8DA
JEDEC	Conforms
JEITA	—
Mass (reference value)	0.085 g

Ordering Information

Part Name	Quantity	Shipping Container
HAT2200R-EL-E	2500pcs	Taping

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